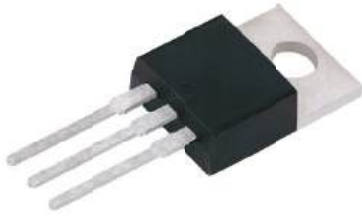
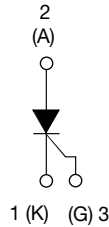


## Thyristor High Voltage, Phase Control SCR, 25 A


**3L TO-220AB**


### FEATURES

- Designed and qualified according to JEDEC®-JESD 47
- 125 °C max. operating junction temperature
- Material categorization:  
for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

### APPLICATIONS

- Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

### DESCRIPTION

The VS-25TTS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	16 A
$V_{DRM}/V_{RRM}$	800 V, 1200 V
$V_{TM}$	1.25 V
$I_{GT}$	45 mA
$T_J$	-40 °C to 125 °C
Package	3L TO-220AB
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter $T_A = 55\text{ °C}$ , $T_J = 125\text{ °C}$ , common heatsink of 1 °C/W	18	22	A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
$I_{RMS}$		25	
$V_{RRM}/V_{DRM}$		800, 1200	V
$I_{TSM}$		320	A
$V_T$	16 A, $T_J = 25\text{ °C}$	1.25	V
dV/dt		500	V/μs
dI/dt		150	A/μs
$T_J$		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE V	$I_{RRM}/I_{DRM}$ AT 125 °C mA
VS-25TTS08-M3	800	800	10
VS-25TTS12-M3	1200	1200	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
			TYP.	MAX.		
Maximum average on-state current	$I_{T(AV)}$	$T_C = 93\text{ }^\circ\text{C}$ , 180° conduction half sine wave	16		A	
Maximum RMS on-state current	$I_{RMS}$		25			
Maximum peak, one-cycle, non-repetitive surge current	$I_{TSM}$	10 ms sine pulse, rated $V_{RRM}$ applied	270			
		10 ms sine pulse, no voltage reapplied	320			
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied	365		$A^2s$	
		10 ms sine pulse, no voltage reapplied	515			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1$ to 10 ms, no voltage reapplied	5152		$A^2\sqrt{s}$	
Maximum on-state voltage drop	$V_{TM}$	16 A, $T_J = 25\text{ }^\circ\text{C}$	1.25		V	
On-state slope resistance	$r_t$	$T_J = 125\text{ }^\circ\text{C}$	12.0		$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.0		V	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$V_R = \text{Rated } V_{RRM}/V_{DRM}$	$T_J = 25\text{ }^\circ\text{C}$	0.5		mA
			$T_J = 125\text{ }^\circ\text{C}$	10		
Holding current	$I_H$	Anode supply = 6 V, resistive load, initial $I_T = 1$ A, $T_J = 25\text{ }^\circ\text{C}$	-	150		
Maximum latching current	$I_L$	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	200			
Maximum rate of rise of off-state voltage	$dV/dt$	$T_J = T_J \text{ max.}$ , linear to $80\text{ }^\circ\text{C}$ , $V_{DRM} = R_g - k = \text{Open}$	500		$V/\mu s$	
Maximum rate of rise of turned-on current	$di/dt$		150		$A/\mu s$	

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	W	
Maximum average gate power	$P_{G(AV)}$		2.0		
Maximum peak positive gate current	+ $I_{GM}$		1.5	A	
Maximum peak negative gate voltage	- $V_{GM}$		10	V	
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	60		mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	45		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	20		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	2.5		V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0		
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0		
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , $V_{DRM} = \text{Rated value}$	0.25		
Maximum DC gate current not to trigger	$I_{GD}$		2.0		mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	$t_{gt}$	$T_J = 25\text{ }^\circ\text{C}$	0.9	$\mu s$
Typical reverse recovery time	$t_{rr}$	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	$t_q$		110	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		-40 to +125	°C
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	1.1	°C/W
Maximum thermal resistance, junction to ambient	$R_{thJA}$		62	
Typical thermal resistance, case to heatsink	$R_{thCS}$	Mounting surface, smooth and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style 3L TO-220AB	25TTS08	
			25TTS12	

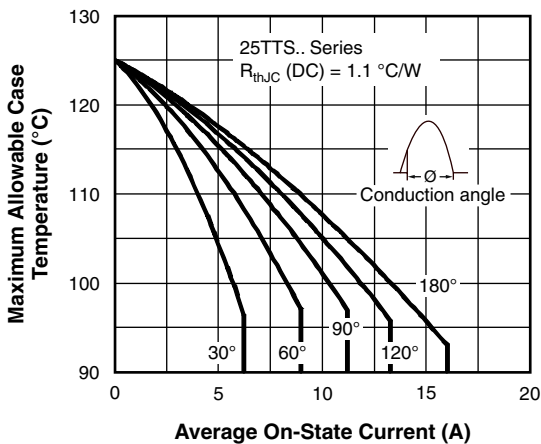


Fig. 1 - Current Rating Characteristics

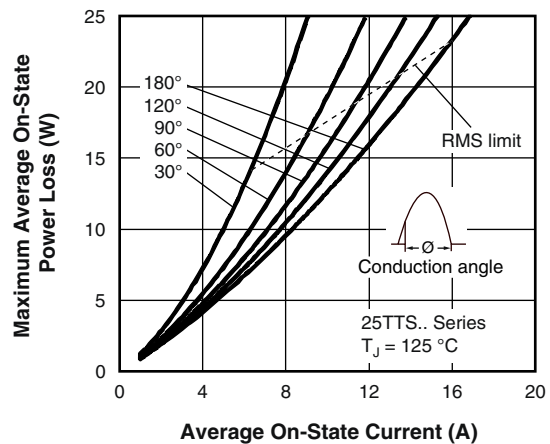


Fig. 3 - On-State Power Loss Characteristics

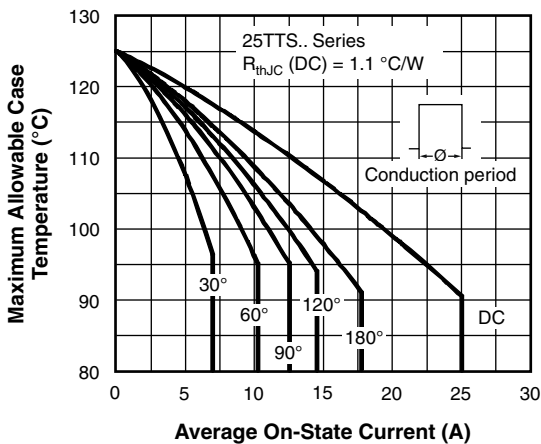


Fig. 2 - Current Rating Characteristics

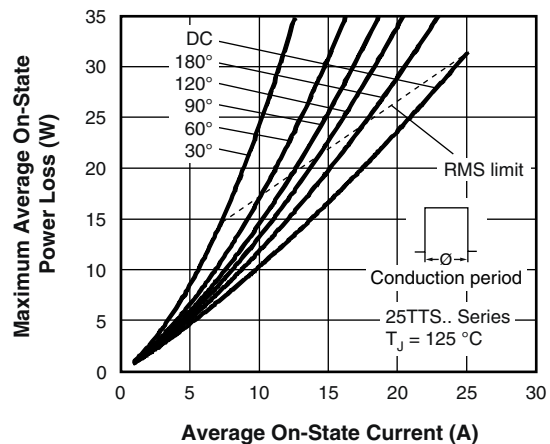


Fig. 4 - On-State Power Loss Characteristics

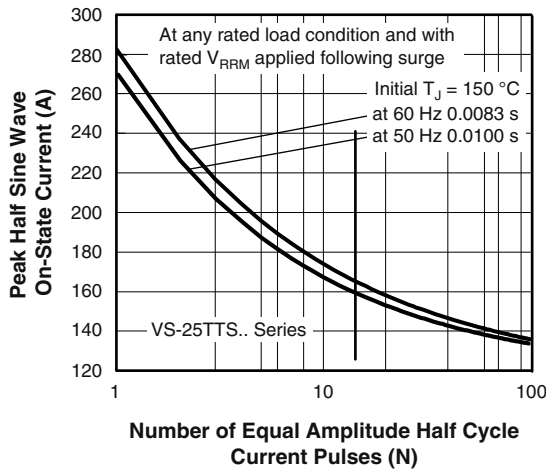


Fig. 5 - Maximum Non-Repetitive Surge Current

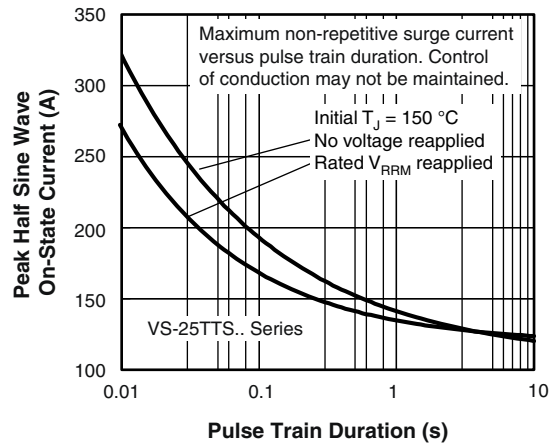


Fig. 6 - Maximum Non-Repetitive Surge Current

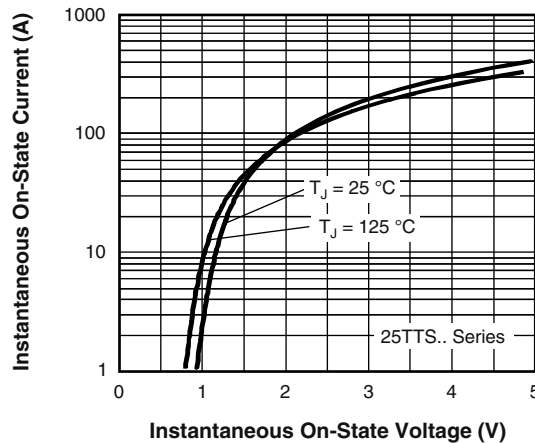


Fig. 7 - On-State Voltage Drop Characteristics

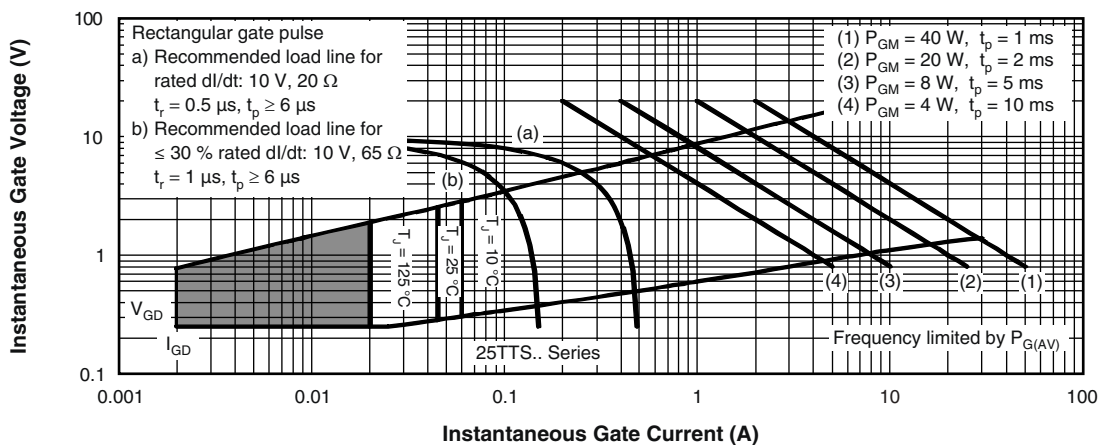


Fig. 8 - Gate Characteristics

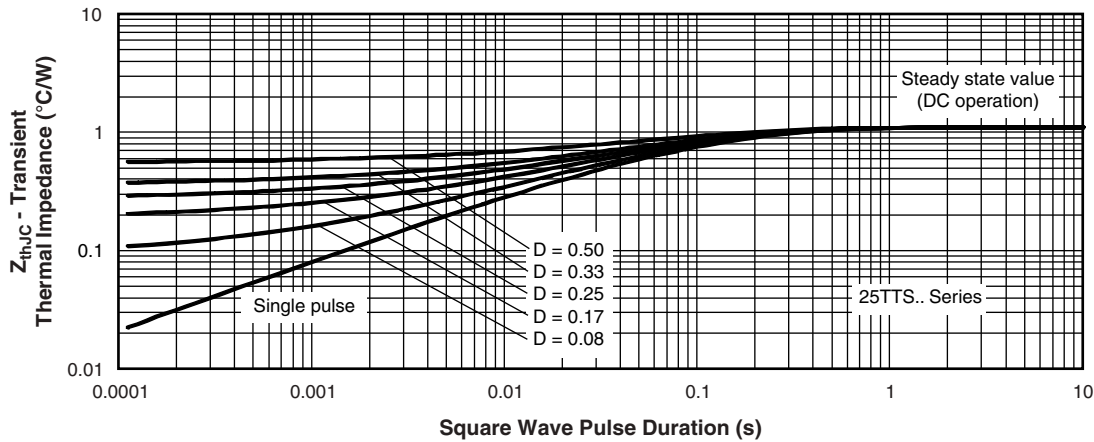


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

**ORDERING INFORMATION TABLE**

Device code	<b>VS-</b>	<b>25</b>	<b>T</b>	<b>T</b>	<b>S</b>	<b>12</b>	<b>-M3</b>
	①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - Current rating (25 = 25 A)
- 3** - Circuit configuration:  
T = single thyristor
- 4** - Package:  
T = TO-220AB
- 5** - Type of silicon:  
S = standard recovery rectifier
- 6** - Voltage rating 08 = 800 V  
12 = 1200 V
- 7** - Environmental digit:  
-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

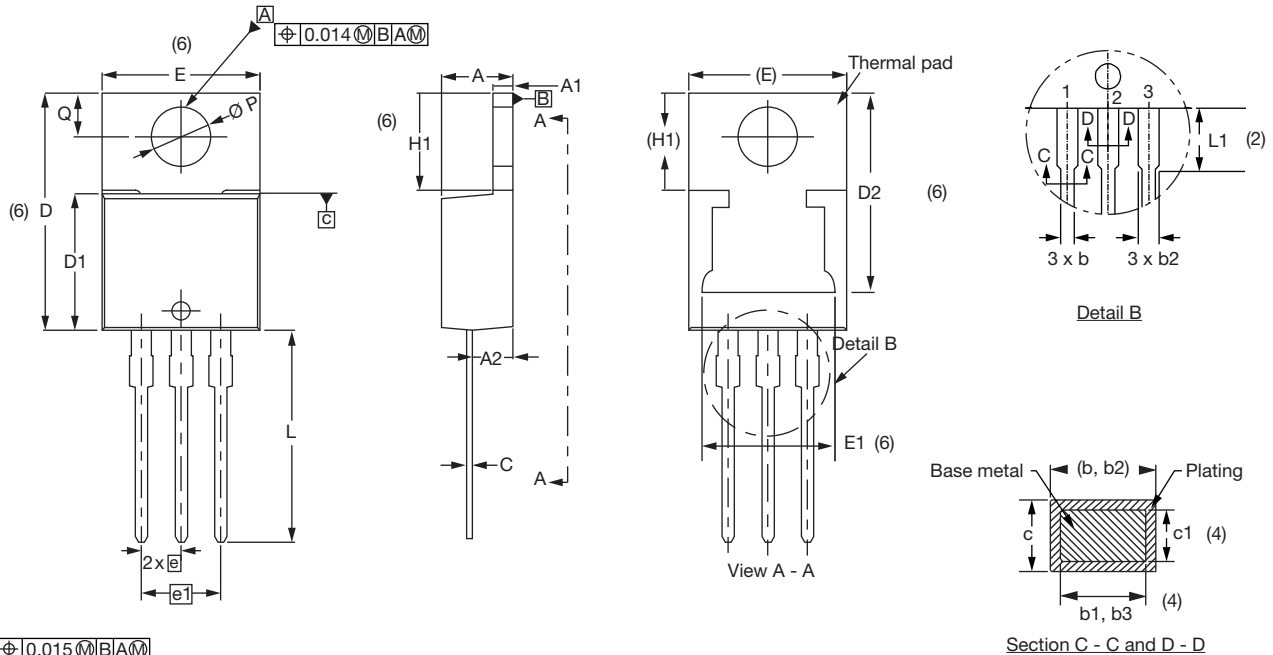
<b>ORDERING INFORMATION (Example)</b>			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-25TTS08-M3	50	1000	Antistatic plastic tubes
VS-25TTS12-M3	50	1000	Antistatic plastic tubes

<b>LINKS TO RELATED DOCUMENTS</b>	
Dimensions	<a href="http://www.vishay.com/doc?96154">www.vishay.com/doc?96154</a>
Part marking information	<a href="http://www.vishay.com/doc?95028">www.vishay.com/doc?95028</a>



### 3L TO-220AB

**DIMENSIONS** in millimeters and inches



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183		D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055		E	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115		E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040		e	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4	e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068		H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4	L	13.52	14.02	0.532	0.552	
c	0.36	0.61	0.014	0.024		L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4	∅ P	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3	Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355							

**Notes**

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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